

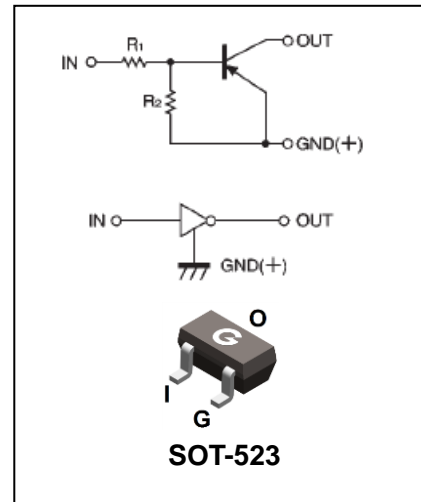
Digital Transistor

DTA(R₁≠R₂ SERIES)E

FEATURES

- Epitaxial planar die construction
- Complementary NPN types available(DTC)
- Built-in biasing resistors, R₁≠R₂
- Also available in lead free version

HF



APPLICATIONS

- The PNP style digital transistor

ORDERING INFORMATION

Type No.	Marking	Package Code
DTA113ZE	E11	SOT-523
DTA114WE	74	SOT-523
DTA114YE	54	SOT-523
DTA123JE	E32	SOT-523
DTA123YE	52	SOT-523
DTA143XE	33	SOT-523
DTA143ZE	E13	SOT-523

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CC}	Supply Voltage	-50	V
V _{IN}	Input Voltage	DTA113ZE	+5 to -10
		DTA114WE	+10 to -30
		DTA114YE	+6 to -40
		DTA123JE	+5 to -12
		DTA123YE	+5 to -12
		DTA143XE	+7 to -20
		DTA143ZE	+5 to -30
I _o	Output Current	DTA113ZE	-100
		DTA114WE	-100
		DTA114YE	-70
		DTA123JE	-100
		DTA123YE	-100
		DTA143XE	-100
		DTA143ZE	-100
I _c (Max.)	Output current	ALL	-100
P _D	Power Dissipation	150	mW

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R _{θJA}	Thermal Resistance, Junction to Ambient Air *1	306	°C/W
R _{θJC}	Thermal Resistance, Junction to Case *1	152	°C/W
R _{θJL}	Thermal Resistance, Junction to Lead *1	61	°C/W
T _j , T _{stg}	Operating and Storage and Temperature Range	-55 to +150	°C

Note 1: The data tested by surface mounted on a 15mm * 15mm * 1mm FR4-epoxy P.C.B

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT	
Input Voltage	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE DTA143ZE	V _{I(off)}	V _{CC} =-5V, I _O =-100μA	-0.3 -0.8 -0.3 -0.5 -0.3 -0.3 -0.5	-	-	V
Input Voltage	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE DTA143ZE	V _{I(on)}	V _O =-0.3V, I _O =-20mA V _O =-0.3V, I _O =-2mA V _O =-0.3V, I _O =-1mA V _O =-0.3V, I _O =-5mA V _O =-0.3V, I _O =-20mA V _O =-0.3V, I _O =-20mA V _O =-0.3V, I _O =-5mA	-	-	-3 -3 -1.4 -1.1 -3.0 -2.5 -1.3	V
Output Voltage	DTA123JE DTA143ZE DTA114YE ALL Others	V _{O(on)}	I _O /I _I =-5mA/-0.25mA I _O /I _I =-10mA/-0.5mA	-	-0.1	-0.3	V
Input Current	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE DTA143ZE	I _I	V _I =-5V	-	-	-7.2 -0.88 -0.88 -3.6 -3.8 -1.8 -1.8	mA
Output Current		I _{O(off)}	V _{CC} =-50V, V _I =0V	-	-	-0.5	μA
DC Current Gain	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE	G _I	V _O =-5V, I _O =-5mA V _O =-5V, I _O =-10mA V _O =-5V, I _O =-5mA V _O =-5V, I _O =-10mA V _O =-5V, I _O =-10mA V _O =-5V, I _O =-10mA	33 24 68 80 33 30	-	-	

Digital Transistor

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	DTA143ZE		V _O =-5V, I _O =-10mA	80			
Input Resistor	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE DTA143ZE	R ₁ (R ₂)		0.7 7 7 1.54 1.54 3.29 3.29	1 10 10 2.2 2.2 4.7 4.7	1.3 13 13 2.86 2.86 6.11 6.11	kΩ
Resistance Ratio	DTA113ZE DTA114WE DTA114YE DTA123JE DTA123YE DTA143XE DTA143ZE	R ₂ /R ₁		8 0.37 3.7 17 3.6 1.7 8	10 0.47 4.7 21 4.5 2.1 10	12 0.57 5.7 26 5.5 2.6 12	-
Gain-Bandwidth Product		f _T	V _{CE} =-10V, I _E =5mA, f=100MHz	-	250	-	MHz

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

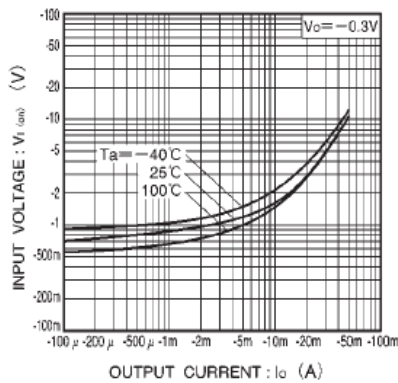


Fig.1 Input voltage vs. output current (ON characteristics)

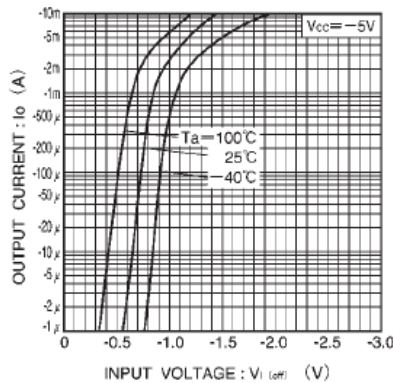


Fig.2 Output current vs. input voltage (OFF characteristics)

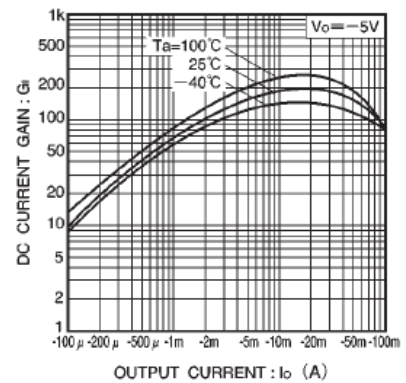


Fig.3 DC current gain vs. output current

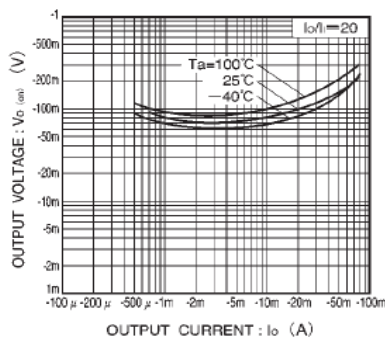


Fig.4 Output voltage vs. output current

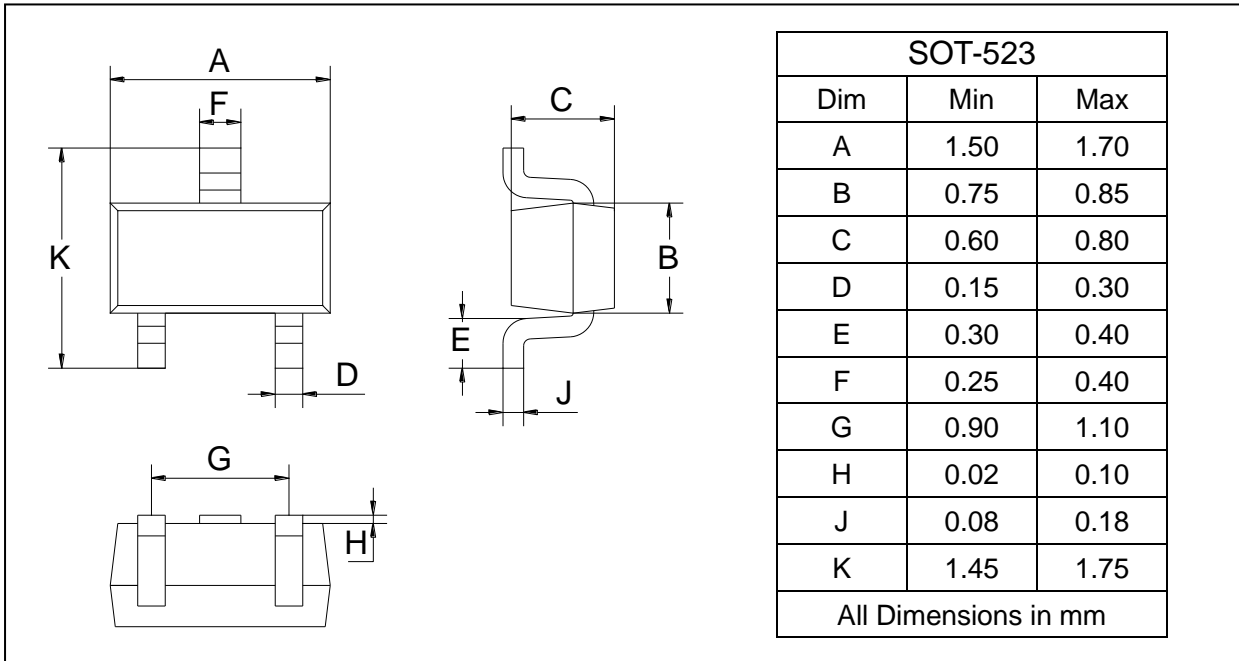
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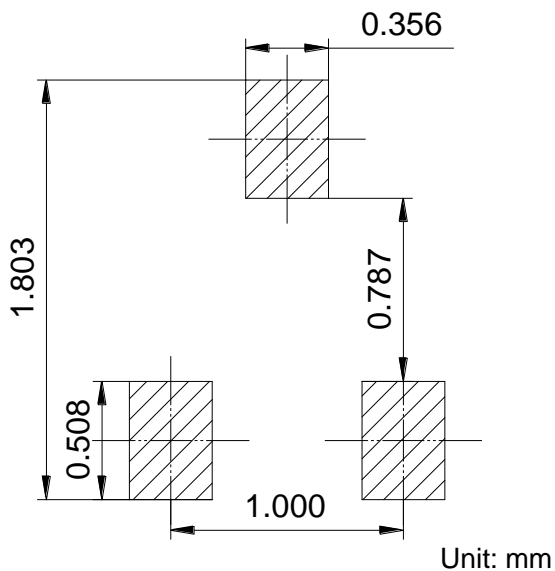
PACKAGE OUTLINE

Plastic surface mounted package

SOT-523



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
DTAXXXE	SOT-523	3000 pcs / Tape & Reel